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Please find below and/or attached an Office communication concerning this application or proceeding.

The time period for reply, if any, is set in the attached communication.

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	Application No.	Applicant(s)
	10/590,901	SCHWARZBAUER, HERBERT
Office Action Summary	Examiner	Art Unit
	RON POMPEY	2812
The MAILING DATE of this communication app Period for Reply	pears on the cover sheet with the d	correspondence address
A SHORTENED STATUTORY PERIOD FOR REPL' WHICHEVER IS LONGER, FROM THE MAILING D. - Extensions of time may be available under the provisions of 37 CFR 1.1 after SIX (6) MONTHS from the mailing date of this communication. - If NO period for reply is specified above, the maximum statutory period or - Failure to reply within the set or extended period for reply will, by statute Any reply received by the Office later than three months after the mailing earned patent term adjustment. See 37 CFR 1.704(b).	ATE OF THIS COMMUNICATION 36(a). In no event, however, may a reply be tinwill apply and will expire SIX (6) MONTHS from a cause the application to become ABANDONE	N. mely filed the mailing date of this communication. ED (35 U.S.C. § 133).
Status		
1) Responsive to communication(s) filed on <u>02 Ju</u>	action is non-final.	
Disposition of Claims		
4) ☐ Claim(s) 27-29,32,34,35,37-52,54 and 56-61 is 4a) Of the above claim(s) is/are withdray 5) ☐ Claim(s) is/are allowed. 6) ☐ Claim(s) 27-29, 32, 34, 35, 37-52, 54 and 56-6 7) ☐ Claim(s) is/are objected to. 8) ☐ Claim(s) are subject to restriction and/o	wn from consideration.	
Application Papers		
9) ☐ The specification is objected to by the Examine 10) ☑ The drawing(s) filed on 26 August 2006 is/are: Applicant may not request that any objection to the Replacement drawing sheet(s) including the correct 11) ☐ The oath or declaration is objected to by the Example 11.	a)⊠ accepted or b)□ objected drawing(s) be held in abeyance. Se tion is required if the drawing(s) is ob	e 37 CFR 1.85(a). ejected to. See 37 CFR 1.121(d).
Priority under 35 U.S.C. § 119		
12) Acknowledgment is made of a claim for foreign a) All b) Some * c) None of: 1. Certified copies of the priority document 2. Certified copies of the priority document 3. Copies of the certified copies of the priority application from the International Bureau * See the attached detailed Office action for a list	s have been received. s have been received in Applicat rity documents have been receive u (PCT Rule 17.2(a)).	ion No ed in this National Stage
Attachment(s) 1) Notice of References Cited (PTO-892) 2) Notice of Draftsperson's Patent Drawing Review (PTO-948) 3) Information Disclosure Statement(s) (PTO/SB/08) Paper No(s)/Mail Date	4) Interview Summary Paper No(s)/Mail D 5) Notice of Informal F 6) Other:	ate

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DETAILED ACTION

Claim Rejections - 35 USC § 102

1. The following is a quotation of the appropriate paragraphs of 35 U.S.C. 102 that form the basis for the rejections under this section made in this Office action:

A person shall be entitled to a patent unless -

- (b) the invention was patented or described in a printed publication in this or a foreign country or in public use or on sale in this country, more than one year prior to the date of application for patent in the United States.
- 2. Claim 58 is rejected under 35 U.S.C. 102(b) as being anticipated by **Fjelstad** (US 6284563).
- 3. **Fjelstad** discloses the limitations of:

In re Claim 58: (New) A method for producing a system, comprising:

providing a component (110, fig. 1A) on a substrate, the component having an electrical contact surface;

producing an insulating layer (130, fig. 1B) on the component, the insulating layer having an opening to expose and surround a portion of the contact surface of the component so that the contact surface is freely accessible, the insulating layer having a lateral surface that defines the opening, the insulating layer being produced by a process comprising:

laminating a first partial insulating layer (130, fig. 1B) on the component and the substrate, the first partial insulating layer having an opening with a first width; and

laminating a second partial insulating layer (140, fig. 1C) on the first partial insulating layer, the second partial insulating layer having an opening with a second width greater than the first width such that a stepped structure is formed from the

contact surface to the first partial insulating layer and from the first partial insulating layer to the second partial insulating layer, the lateral surface being formed as part of the stepped structure; and

locate a metallization layer (170, fig. 1E) of a connecting lead on the lateral surface of the insulating layer in such a way that the metallization layer meets the contact surface (110, fig. 1E) at an angle less than 90 degrees.

Claim Rejections - 35 USC § 103

- 4. The following is a quotation of 35 U.S.C. 103(a) which forms the basis for all obviousness rejections set forth in this Office action:
 - (a) A patent may not be obtained though the invention is not identically disclosed or described as set forth in section 102 of this title, if the differences between the subject matter sought to be patented and the prior art are such that the subject matter as a whole would have been obvious at the time the invention was made to a person having ordinary skill in the art to which said subject matter pertains. Patentability shall not be negatived by the manner in which the invention was made.
- Claims 27, 29, 34-35, 37-39, 42, 46-47 and 52-56 are rejected under 35
 U.S.C. 103(a) as being unpatentable over Nicholas (US 4546534), in view of Guthrie et al. (US 3495324).
- 6. **Nicholas** discloses the limitations of:

In re Claim 27: A system comprising:

an electrical component (fig. 2) provided with at least one electrical contact surface (14, fig. 2);

an electrical insulating layer (2, fig. 12/15, fig. 13), which is disposed on the component, the electrical insulating layer having an opening (16 and 17, fig. 14) to

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expose and surround a portion of the contact surface (14, fig. 2), the insulating layer having a lateral surface that delimits the opening (14, fig. 2), and

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an electrical connecting lead (20 and 21, fig. 2) for electrically contacting the contact surface of the component, the electrical connecting lead comprising <u>first and</u> metallization layer, the <u>first metallization layer being</u> (20 and 21, fig. 2) located on the lateral surface, such that the <u>first metallization layer meets</u> the contact surface (13 and 14, fig. 2) at an angle less than 90 degrees.

In re Claim 29: The system as claimed in claim 27, wherein the <u>first</u> metallization layer (20 and 21, fig. 2) has a layer thickness within a range of from 0.5 µm to 30 µm (1µm; col. 5, lns. 67-68).

In re Claim 34: The system as claimed in claim 27, wherein the insulating (2, figs. 12/14 and 15, figs. 13/14) layer is formed by laminating at least one insulating foil onto the component (15, fig. 13).

In re Claim 35: The system as claimed in claim 34, wherein the lateral surface of the insulating layer faces (inside surfaces of layer 2/15, fig. 14) the component (the IGFET (11/13/14), fig. 14),

at least one part of the insulating foil (15, fig. 13; col. 5, Ins. 57-62) is laminated onto the component (the IGFET(11/13/14), fig. 14) in such a way that the insulating layer has a surface contour facing away from the component, and

a surface contour of the component is shown in the surface contour of the insulating foil that faces away from the component.

In re Claim 38: The system as claimed in claim 37, wherein the <u>first and/or second</u> metallization layer (20/21, fig. 2) and/or the section is formed of at least one metal selected from the group consisting of aluminum, gold, copper, molybdenum, silver, titanium and tungsten (aluminum, col. 5, Ins. 67-68).

In re Claim 39: The system as claimed in claim 36, wherein the component is a semiconductor component (the IGFET (11/13/14), fig. 14).

In re Claim 42: The system as claimed in claim 27, wherein the insulating layer has a plurality of openings arranged in a row or a matrix (openings 16 and 17 are in a row, fig. 1).

In re Claim 46: A method for producing a system comprising:

providing a component (IGFET (11/13/14), fig. 2) with an electrical contact surface (13 and 14, fig. 2);

producing an insulating layer (2, fig. 12/15, fig. 13) on the component, the insulating layer having an opening (16 and 17, fig. 14) to expose and surround a portion of the contact surface (13 and 14, fig. 14) of the component so that the contact surface is freely accessible, the insulating layer having a lateral surface that defines the opening; and

forming a metallization layer (20 and 21, fig. 2) of a connecting lead on the lateral surface of the insulating layer in such a way that the metallization layer meets the contact surface at an angle less than 90 degrees:

In re Claim 47: The method as claimed in claim 46, wherein the insulating layer is formed by a process comprising: laminating at least one insulating foil (15, fig. 13) onto

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the component (IGFET (11/13/14), fig. 13; and producing an opening (16 and 17, fig. 14) in the insulating foil so that the contact surface (13/14, fig. 14) of the component is exposed.

In re Claim 52: The method as claimed in claim 46, wherein the metallization layer and/or the insulating layer is formed by a vapor deposition method (evaporation, col. 2, lns. 67 - 68).

7. **Nicholas**, as indicated above, discloses all the features of the claims **except**:

In re Claim 27: wherein the electrical connecting lead comprising a <u>second</u> metallization layers, the second metallization layer being formed of a material different from the first metallization layer, the second metallization layer being formed on the insulating layer and outside of the opening in the insulating layer, the second metallization layer having a thickness greater than that of the first metallization layer.

In re Claim 37: The system as claimed in claim 36, wherein the <u>second</u> metallization layer is electrodeposited.

In re Claim 46: wherein <u>after forming the metallization layer, masking the opening</u> in the insulating layer; and

forming a section of the connecting lead separately from the metallization layer, the section of the connecting lead being produced on the insulating layer while the opening in the insulating layer is masked such that the section of the connecting lead is formed outside of the opening in the insulating layer, the section of the connecting lead having a thickness which exceeds that of the metallization layer.

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In re Claim 54: The method as claimed in Claim <u>46</u>, wherein a metal is electrodeposited to produce the section on the insulating layer.

In re Claim 56: (New) The method as claimed in claim 46, wherein the section of the connecting lead is formed from a different material from the metallization layer.

a. However, **Guthrie discloses**:

In re Claim 27: wherein the electrical connecting lead comprising a <u>second</u> metallization layers (16/17/25, fig. 4), the <u>second metalization layer being formed of a material</u> (copper 17/25, fig. 4) different from the first metallization layer (aluminum 13, fig. 4), the <u>second metallization layer being formed on the insulating layer</u> (12, fig. 4) and outside of the opening (opening where contact 11 and 13 first metallization are connected, fig. 4) in the insulating layer, the <u>second metallization layer</u> (16/17/25, fig. 4) having a thickness greater than that of the first metallization layer (13, fig. 4).

In re Claim 37: The system as claimed in claim 36, wherein the <u>second</u> metallization layer is electrodeposited (col. 4, lns. 1-18).

In re Claim 46: wherein <u>after forming the metallization layer (13, fig. 4), masking</u>
(14, fig. 4) the opening in the insulating layer; and

forming a section (16/17/25, fig. 4) of the connecting lead separately from the metallization layer (13, fig. 4), the section of the connecting lead being produced on the insulating layer (12, fig. 4) while the opening in the insulating layer is masked such that the section of the connecting lead is formed outside of the opening in the insulating

layer, the section of the connecting lead having a thickness which exceeds that of the metallization layer.

In re Claim 54: The method as claimed in Claim <u>46</u>, wherein a metal is electrodeposited to produce the section on the insulating layer (col. 4, lns. 1-18).

In re Claim 56: (New) The method as claimed in claim 46, wherein the section (copper 17/25, fig. 4) of the connecting lead is formed from a different material from the metallization layer (aluminum 13, fig. 4).

Therefore, it would have been obvious to one of ordinary skill in the art at the time of the invention to modify the connecting lead in **Nicholas**, with second metallization layers or section of the connecting lead is formed separately from the metallization layer, the second metallization layers or section of the connecting lead being produced on the insulating layer while the opening in the insulating layer is masked such that the section of the connecting lead is formed outside of the opening in the insulating layer, the section of the connecting lead having a thickness which exceeds that of the metallization layer (In re claims 27, 46 and 56) and wherein the section of the connecting lead is electrodeposited (In re claims 37 and 54) by **Guthrie**, because this will provide for fine pattern resolution and electrodes can be selectively formed in various positions, when a section of the connecting lead is formed outside of the opening in the insulating layer; therefore the increase in the degree of freedom of connection between external equipment and the semiconductor package is improved.

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8. Claims 28 and 43 rejected under 35 U.S.C. 103(a) as being unpatentable over **Nicholas** in view of **Guthrie** as applied to claim 27 above, in view of **Seales** (US 3945030).

9. **Nicholas and Guthrie**, as indicated above, discloses all the features of the claims **except**:

In re Claim 28: The system as claimed in claim 27, wherein the <u>first</u> metallization layer is oriented at an angle to the contact surface within a range of from 30° to 80°.

In re Claim 43: (New) The system as claimed in claim 27, wherein the <u>first</u> metallization layer is oriented at an angle to the contact surface within a range of from 50° to 70°.

b. However, **Seales discloses**:

In re Claim 28: (New) The system as claimed in claim 27, wherein the <u>first</u> metallization layer (96/97.98, fig. 13) is oriented at an angle to the contact surface within a range of from 30° to 80° (col. 1, lns. 55-68).

In re Claim 43: (New) The system as claimed in claim 27, wherein the <u>first</u> metallization layer is oriented at an angle to the contact surface within a range of from 50° to 70° (col. 1, lns. 55-68).

Therefore, it would have been obvious to one of ordinary skill in the art at the time of the invention to modify the orientation angle of the metallization layer in **Nicholas** and **Guthrie**, with metallization layer being oriented at an angle to the contact

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surface within a range of from 30° to 80° as taught by **Seales**, because it makes it possible to obtain excellent contact metallization as disclosed in column 2, lines 24-28.

- 10. Claims 32 and 44-45 are rejected under 35 U.S.C. 103(a) as being unpatentable over **Nicholas** in view of **Guthrie** as applied to claim 27 above.
- 11. **Nicholas and Guthrie**, as indicated above, discloses all the features of the claims **except**:

In re Claim 32: The system as claimed in claim 27, wherein the insulating layer has a layer thickness within a range of from 20 μ m to 500 μ m.

In re Claim 44: The system as claimed in claim 27, wherein the <u>first</u> metallization layer has a layer thickness within a range of from 2.0 µm to 20 µm.

In re Claim 45: (New) The system as claimed in claim 27, wherein the insulating layer has a layer thickness within a range of from 50 µm up to and including 200 µm.

a. However, it would have been obvious to one of ordinary skill in the art at the time the invention to modify the thickness of the insulating and metallization layer in Nicholas, with the insulating layer having a thickness within a range of from 20 μ m to 500 μ m(In re Claim 32) or 50 μ m up to an including 200 μ m(In re Claim 45) and the metallization layer having a thickness within a range of from 2.0 μ m to 20 μ m(In re Claim 44) as claimed, because the thicker insulator will reduce hot carrier which increase reliability of the device and thicker metal layer will last longer under electrical and thermal stresses to make the device more durable, since it has been held that

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where the general conditions of a claim are disclosed in prior art, discovering the optimum or working ranges involves only routine skill in the art. In re Aller,105 USPQ 233.

- 12. Claims 40 and 41 rejected under 35 U.S.C. 103(a) as being unpatentable over **Nicholas** in view of **Guthrie** as applied to claim 39 above, in view of Admitted Prior Art (APA).
- **13. Nicholas** and **Guthrie**, as indicated above, discloses all the features of the claims **except**:

In re Claim 40: (New) The system as claimed in claim 39, wherein the semiconductor component is a power semiconductor component.

In re Claim 41: (New) The system as claimed in claim 40, wherein the power semiconductor component is a component selected from the group consisting of a diode, a MOSFET, a IGBT, a thyristor and a bipolar transistor.

c. However, APA discloses:

In re Claim 40: (New) The system as claimed in claim 39, wherein the semiconductor component is a power semiconductor component ([0003]).

In re Claim 41: (New) The system as claimed in claim 40, wherein the power semiconductor component is a component selected from the group consisting of a diode, a MOSFET, a IGBT, a thyristor and a bipolar transistor ([0003]).

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Therefore, it would have been obvious to one of ordinary skill in the art at the time of the invention to modify the integrated circuit(IC) in Nicholas, with the power semiconductor component as taught by APA, because Nicholas is silent to what kind of IC is being formed.

- 14. Claims 48 and 49 are rejected under 35 U.S.C. 103(a) as being unpatentable over **Nicholas** in view of **Guthrie** as applied to claim 46 above, in view of Neugenbauer et al. (US 5291066).
- 15. **Nicholas** and **Guthrie**, as indicated above, discloses all the features of the claims **except**:

In re Claim 48: The method as claimed in claim 47, wherein the insulating foil is laminated under a partial vacuum.

In re Claim 49: The method as claimed in claim 47, wherein the opening in the insulating foil is made by laser ablation.

d. However, Neugenbauer discloses:

In re Claim 48: The method as claimed in claim 47, wherein the insulating foil (18/20, figs. la and 3b) is laminated under a partial vacuum (cvd, ALE, col. 7, Ins. 5 - 22).

In re Claim 49: The method as claimed in claim 47, wherein the opening (25, figs. la and 3a) in the insulating foil is made by laser ablation (col. 8, Ins. 31-51).

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Therefore, it would have been obvious to one of ordinary skill in the art at the time of the invention to modify how the insulating foil is laminated and how the opening in the insulating foil is made in **Nicholas** and **Guthrie**, with the insulating foil being laminated under a partial vacuum (In re Claim 48) and forming the opening in the insulating foil by laser ablation (In re Claim 49) taught by **Neugenbauer**, because Nicholas is silent to particulars of how the insulating foil is laminated and how the opening in the insulating foil is made.

- 16. Claims 50 and 51 are rejected under 35 U.S.C. 103(a) as being unpatentable over **Nicholas** in view of **Guthrie** as applied to claim 46 above, in view of **Kao** et al. (US 6338361).
- 17. **Nicholas** and **Guthrie**, as indicated above, discloses all the features of the claims **except**:

In re Claim 50: The method as claimed in claim 46, wherein in order to produce the insulating layer on the component, a compressed air process is used wherein paint is applied to the component.

In re Claim 51: The method as claimed in claim 50, wherein the paint is a photosensitive paint.

e. However, Kao discloses:

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In re Claim 50: (New) The method as claimed in claim 46, wherein in order to produce the insulating layer (photoresist) on the component, a compressed air process is used wherein paint is applied to the component (col. 3, lns. 27-45).

In re Claim 51: (New) The method as claimed in claim 50, wherein the paint is a photo-sensitive paint (photoresist; col. 3, Ins. 27 - 45).

Therefore, it would have been obvious to one of ordinary skill in the art at the time of the invention to modify the insulating layer and how it is formed in **Nicholas** and **Guthrie**, with the photoresist paint method as taught by **Kao**, because using a photoresist as the insulating layer reduces steps, via a separate masking step is not need to form the opening in the insulating layer, which reduces cost of making the device.

- 18. Claim 57 is rejected under 35 U.S.C. 103(a) as being unpatentable over **Nicholas** in view of **Guthrie** as applied to claim 46 above, in view of **Huang** (US 6452270).
- 19. **Nicholas** and **Guthrie** discloses the features of the claims:

In re Claim 57: (New) The system as claimed in claim 27, the second metallization layer is formed of copper or aluminum (Nicholas: aluminum, col. 5, lns. 67-68 or **Guthrie**: aluminum/copper/copper 16/17/25, fig. 4).

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20. **Nicholas** and **Guthrie**, as indicated above, discloses all the features of the claims **except**:

In re Claim 57: (New) The system as claimed in claim 27, wherein the first metallization layer is formed of a titanium tungsten alloy.

f. However, Huang discloses:

In re Claim 57: (New) The system as claimed in claim 27, wherein the first metallization layer is formed of a titanium tungsten alloy (titanium tungsten (TiW) col.1, ln. 50).

Therefore, it would have been obvious to one of ordinary skill in the art at the time of the invention to modify the metallization layer in **Nicholas** and **Guthrie**, with the metallization layer is formed of a titanium tungsten alloy (TiW) as taught by **Huang**, because titanium tungsten alloy (TiW) is good for a barrier layer in package bonding.

- 21. Claims 59 and 60 are rejected under 35 U.S.C. 103(a) as being unpatentable over **Fjelstad** as applied to claim 58 above, in view of **Neugenbauer** et al. (US 5291066).
- 22. Fjelstad, as indicated above, discloses all the features of the claims except:
 In re Claim 59: (New) The method as claimed in claim 58, wherein the insulating foil is laminated under a partial vacuum.

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In re Claim 60: (New) The method as claimed in claim 58, wherein the opening in the insulating foil is made by laser ablation.

g. However, Neugenbauer discloses:

In re Claim 59: The method as claimed in claim 47, wherein the insulating foil (18/20, figs. la and 3b) is laminated under a partial vacuum (cvd, ALE, col. 7, Ins. 5 - 22).

In re Claim 60: The method as claimed in claim 47, wherein the opening (25, figs. la and 3a) in the insulating foil is made by laser ablation (col. 8, Ins. 31-51).

Therefore, it would have been obvious to one of ordinary skill in the art at the time of the invention to modify how the insulating foil is laminated and how the opening in the insulating foil is made in **Fjelstad**, with the insulating foil being laminated under a partial vacuum (In re Claim 59) and forming the opening in the insulating foil by laser ablation (In re Claim 60) taught by **Neugenbauer**, because Fjelstad is silent to particulars of how the insulating foil is laminated and how the opening in the insulating foil is made.

- 23. Claim 61 is rejected under 35 U.S.C. 103(a) as being unpatentable over **Fjelstad** as applied to claim 58 above, in view of **Guthrie**.
- 24. Fjelstad, as indicated above, discloses all the features of the claims except:

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In re Claim 61: (New) The method as claimed in claim 58, wherein the metallization layer is formed by a vapor deposition method.

h. However, Guthrie discloses:

In re Claim 61: (New) The method as claimed in claim 58, wherein the metallization layer is formed by a vapor deposition method (forming metallization layer by evaporation, col.1, lns. 67 - 68).

Therefore, it would have been obvious to one of ordinary skill in the art at the time of the invention to modify how the metallization layer is formed in **Fjelstad**, with the evaporation method taught by **Guthrie**, because Guthrie discloses an art recognized equivalence of methods, evaporation and sputtering (Guthrie: col. 1, lns. 67-68), to form metallization layer; therefore one of ordinary skill would interchange the sputtering of Fjelstad with the evaporation of Guthrie to form the metal layer.

Response to Arguments

2. Applicant's arguments with respect to claims 27-29, 32, 34, 35, 37-52, 54 and 56-61, received 11/30/09, have been considered but are moot in view of the new ground(s) of rejection.

Conclusion

3. The prior art made of record and not relied upon is considered pertinent to applicant's disclosure.

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Hashimoto (US 6323542) discloses second metallization formed outside of

opening.

Any inquiry concerning this communication or earlier communications from the

examiner should be directed to RON POMPEY whose telephone number is (571)272-

1680. The examiner can normally be reached on 9AM - 5PM.

If attempts to reach the examiner by telephone are unsuccessful, the examiner's

supervisor, Charles Garber can be reached on (571) 272-2194. The fax phone number

for the organization where this application or proceeding is assigned is 571-273-8300.

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/Walter L. Lindsay, Jr./
Primary Examiner, Art Unit 2812

/Ron Pompey/ Examiner, Art Unit 2812

07/31/10